

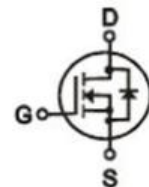
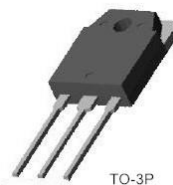
Application

- Switch Mode Power Supply(SMPS)
- Uninterruptible Power Supply(UPS)
- Power Factor Correction (PFC)

- Improved dv/dt Capability
- 100% Avalanche Tested

Product Summary

BVDSS	RDSON	ID
500V	0.14Ω	28A



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM28N50V	AGM20N65V	TO-3P	----	----	1000
AGM28N50T	AGM10N65T	TO-247	-----	----	1000

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Value	Unit
		TO-3P	
Drain-Source Voltage ($V_{GS} = 0V$)	V_{DSS}	500	V
Continuous Drain Current	I_D	28	A
Pulsed Drain Current (note1)	I_{DM}	112	A
Gate-Source Voltage	V_{GSS}	± 30	V
Single Pulse Avalanche Energy (note2)	E_{AS}	500	mJ
Avalanche Current (note1)	I_{AS}	10	A
Repetitive Avalanche Energy (note1)	E_{AR}	300	mJ
Power Dissipation ($T_C = 25^\circ\text{C}$)	P_D	431	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	$^\circ\text{C}$

Thermal Resistance

Parameter	Symbol	Value	Unit
		TO-3P	
Thermal Resistance, Junction-to-Lead	R_{thJL}	0.29	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62	

N-Channel Specifications $T_J = 25^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	500	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 500V, V_{GS} = 0V, T_J = 25^\circ\text{C}$	--	--	1	μA
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30V$	--	--	± 100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	3.0	--	4.0	V
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 14A$	--	0.14	0.18	Ω
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0V,$ $V_{DS} = 25V,$ $f = 1.0\text{MHz}$	--	4155	--	pF
Output Capacitance	C_{oss}		--	445	--	
Reverse Transfer Capacitance	C_{rss}		--	32	--	
Total Gate Charge	Q_g	$V_{DD} = 400V, I_D = 28A,$ $V_{GS} = 10V$	--	109	--	nC
Gate-Source Charge	Q_{gs}		--	20	--	
Gate-Drain Charge	Q_{gd}		--	46	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 250V, I_D = 28A,$ $R_G = 25\Omega$	--	66	--	ns
Turn-on Rise Time	t_r		--	59	--	
Turn-off Delay Time	$t_{d(off)}$		--	427	--	
Turn-off Fall Time	t_f		--	108	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	$T_C = 25^\circ\text{C}$	--	--	28	A
Pulsed Diode Forward Current	I_{SM}		--	--	112	
Body Diode Voltage	V_{SD}	$T_J = 25^\circ\text{C}, I_{SD} = 14A, V_{GS} = 0V$	--	--	1.4	V
Reverse Recovery Time	t_{rr}	$V_{GS} = 0V, I_S = 28A,$ $di_F/dt = 100A/\mu s$	--	482	--	ns
Reverse Recovery Charge	Q_{rr}		--	7.6	--	μC

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $L=10\text{mH}, V_{DD} = 50V, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. Pulse Test: Pulse width $\leq 300\mu s$, Duty Cycle $\leq 1\%$

Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics ($T_J = 25^\circ\text{C}$)

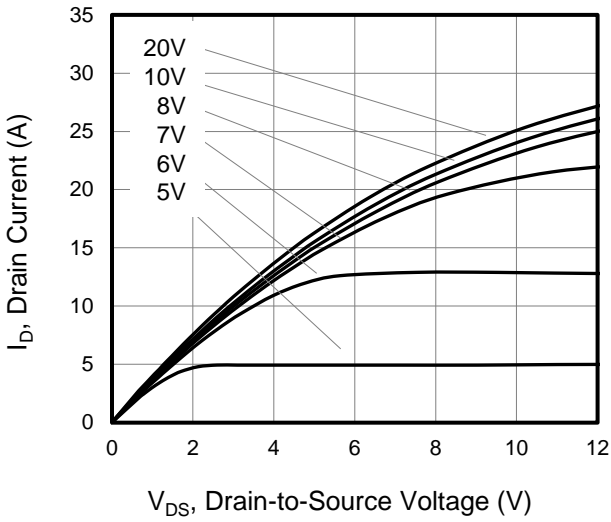


Figure 2. Body Diode Forward Voltage

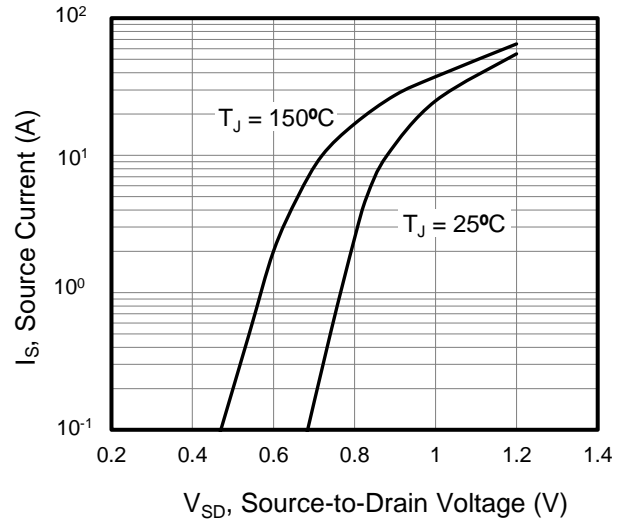


Figure 3. Drain Current vs. Temperature

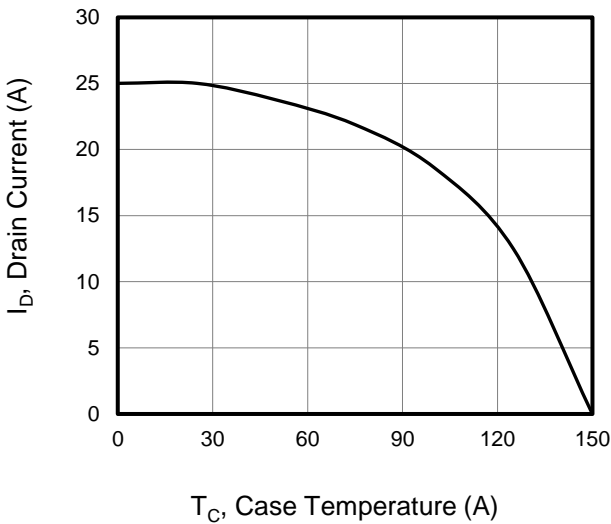


Figure 4. BV_{DSS} Variation vs. Temperature

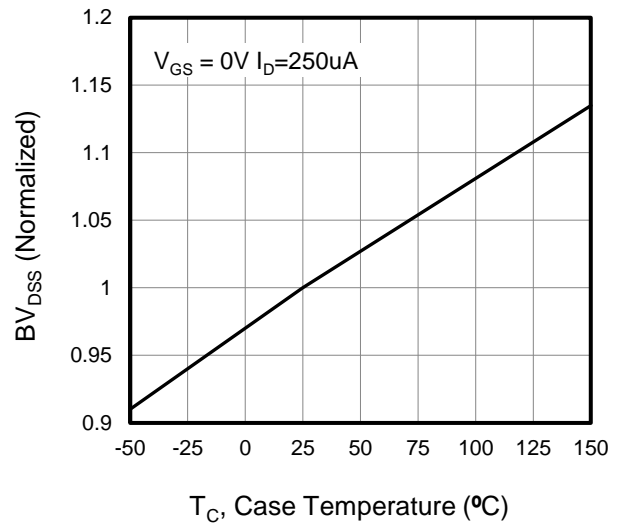


Figure 5. Transfer Characteristics

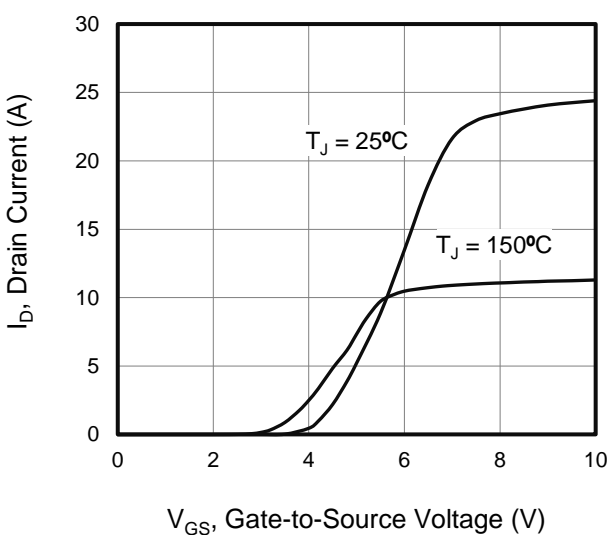
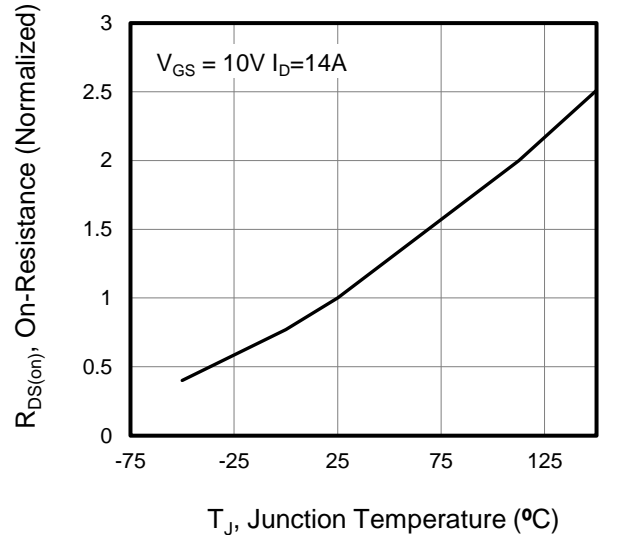


Figure 6. On-Resistance vs. Temperature



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Capacitance

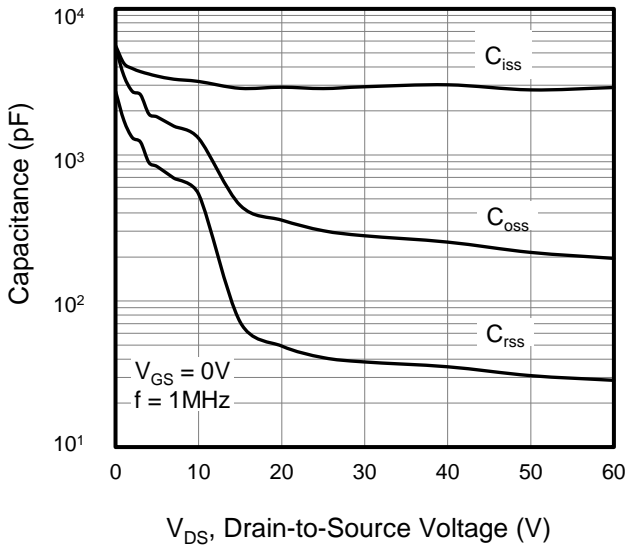


Figure 8. Gate Charge

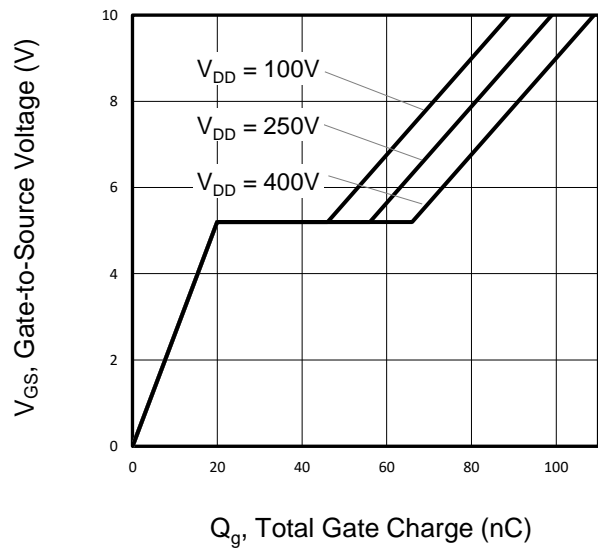


Figure 9. Transient Thermal Impedance

TO-247, TO-3P

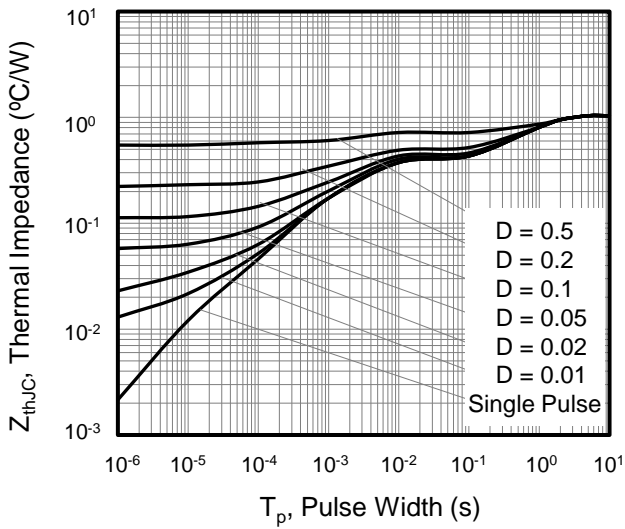


Figure A: Gate Charge Test Circuit and Waveform

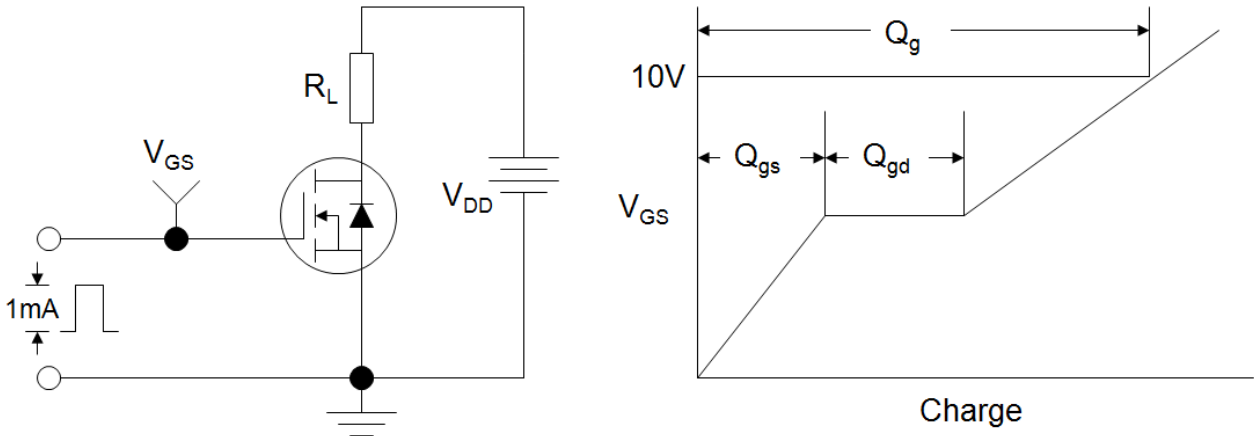


Figure B: Resistive Switching Test Circuit and Waveform

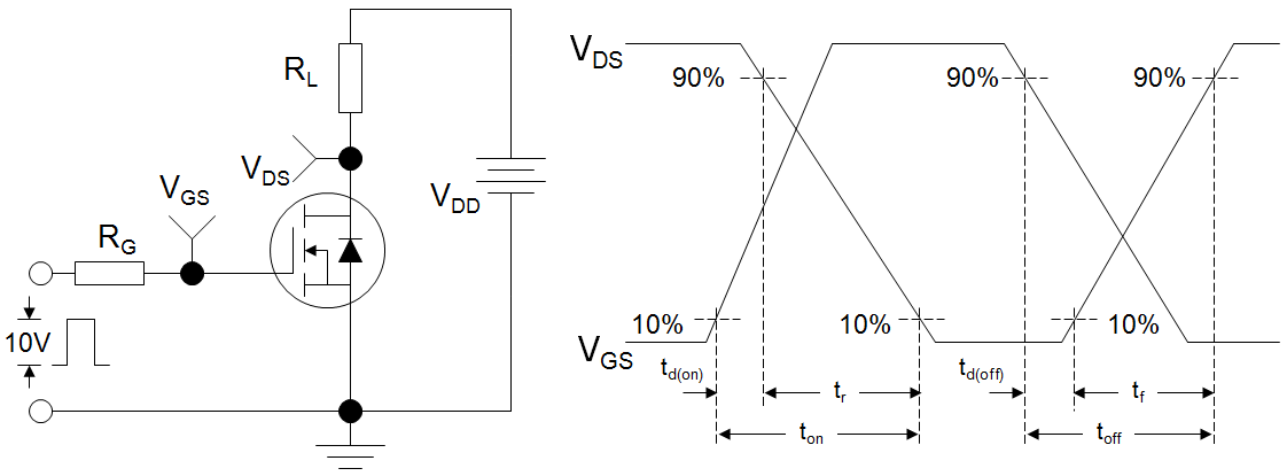
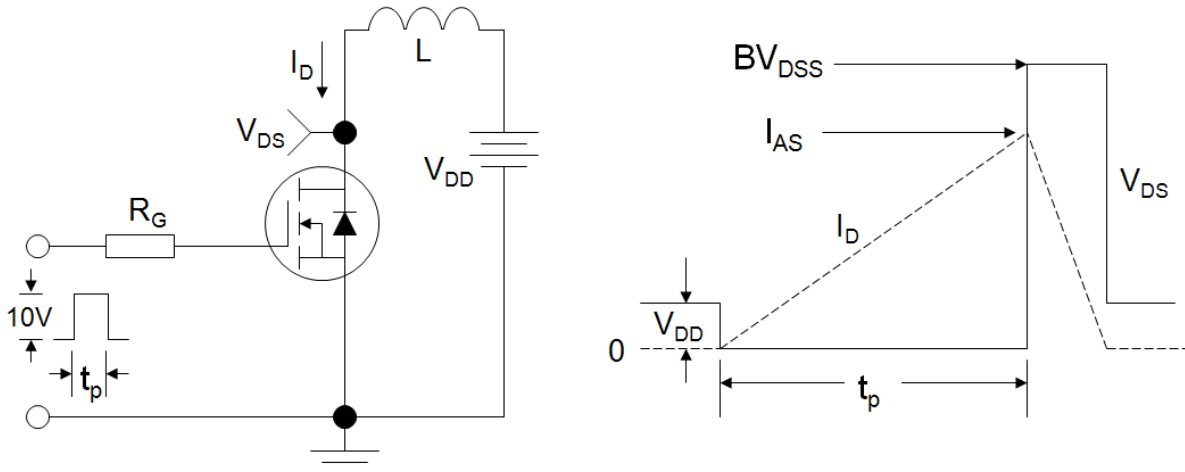
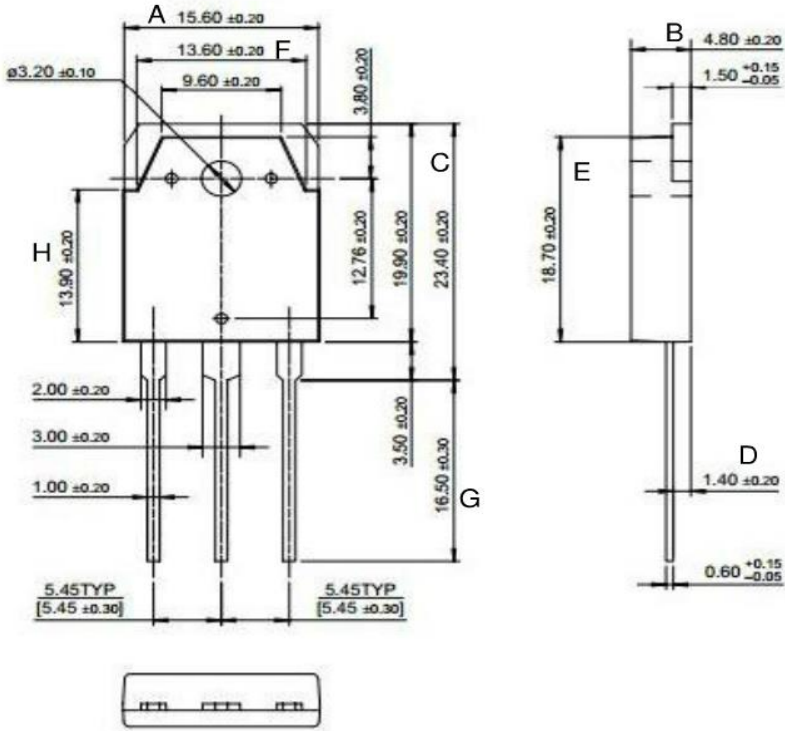


Figure C: Unclamped Inductive Switching Test Circuit and Waveform



TO-3P



Dim	Min	Max
A	15.6	15.8
B	4.75	4.8
C	19.9	20.1
D	1.4	1.6
E	16.8	18.7
F	13.3	13.6
H	13.9	14.16

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